



30NM90-Q

Power MOSFET

30A, 900V N-CHANNEL SUPER-JUNCTION MOSFET

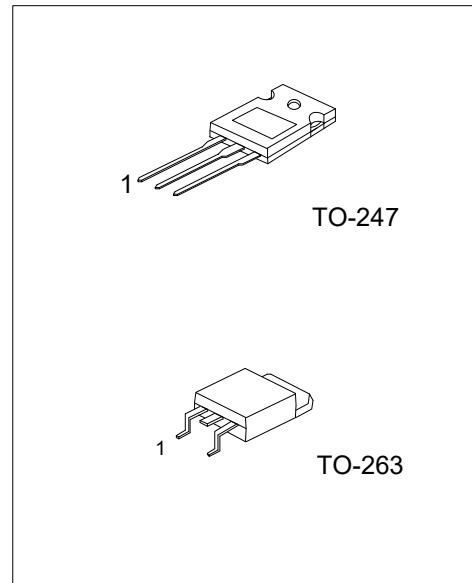
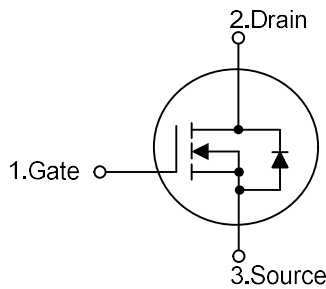
DESCRIPTION

The UTC 30NM90-Q is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 320 \text{ m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=15\text{A}$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL



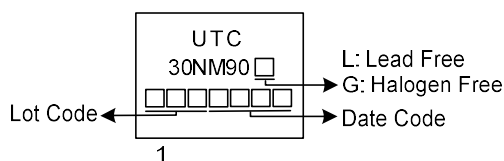
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
30NM90L-T47-T	30NM90G-T47-T	TO-247	G	D	S	Tube
30NM90L-TQ2-T	30NM90G-TQ2-T	TO-263	G	D	S	Tube
30NM90L-TQ2-R	30NM90G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate C: Collector E: Emitter

<p>30NM90G-T47-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) T47: TO-247, TQ2: TO-263</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	900	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	30	A
	Pulsed (Note 2)	I _{DM}	60	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	375	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8.1	V/nS
Power Dissipation	TO-247	P _D	280	W
	TO-263		130	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 30 mH, I_{AS} = 5.0A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C

4. I_{SD} ≤ 30A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-247	θ _{JA}	50	°C/W
	TO-263		62.5	°C/W
Junction to Case	TO-247	θ _{JC}	0.44	°C/W
	TO-263		0.96 (Note)	°C/W

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

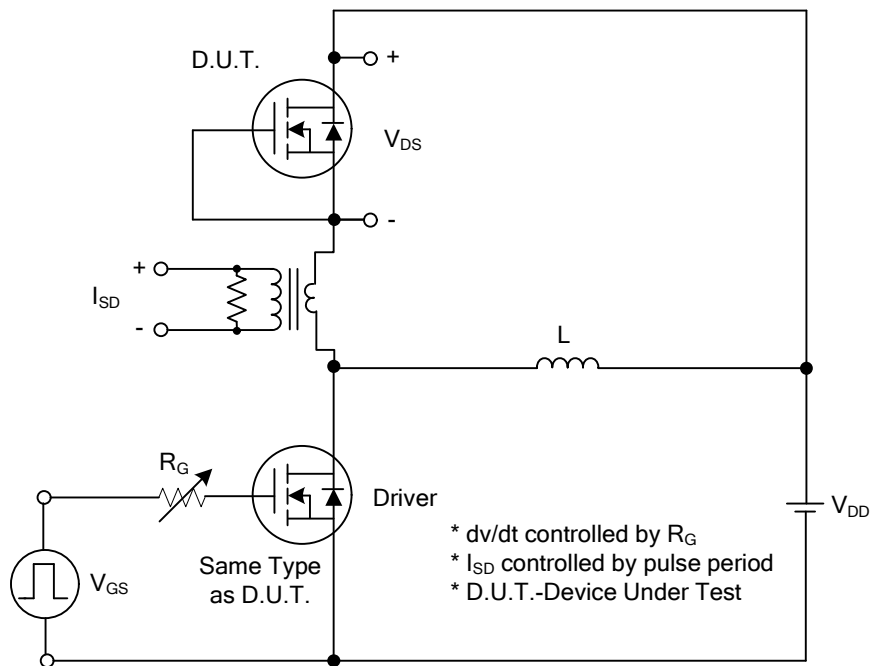
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	900			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=900\text{V}$, $V_{GS}=0\text{V}$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse					
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=15\text{A}$			320	m Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, $f=1.0\text{MHz}$		2600		pF
Output Capacitance	C_{OSS}			140		pF
Reverse Transfer Capacitance	C_{RSS}			1.8		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=720\text{V}$, $V_{GS}=10\text{V}$, $I_D=30\text{A}$ $I_G=1\text{mA}$ (Note1, 2)		92		nC
Gate to Source Charge	Q_{GS}			24		nC
Gate to Drain Charge	Q_{GD}			38		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=100\text{V}$, $V_{GS}=10\text{V}$, $I_D=30\text{A}$, $R_G=25\Omega$ (Note1, 2)		35		ns
Rise Time	t_R			25		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			220		ns
Fall-Time	t_F			58		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				30	A
Maximum Body-Diode Pulsed Current	I_{SM}				60	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=30\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=30\text{A}$, $V_{GS}=0\text{V}$, $dI_F/dt=100\text{A}/\mu\text{s}$		960		ns
Body Diode Reverse Recovery Charge	Q_{rr}			23.1		μC

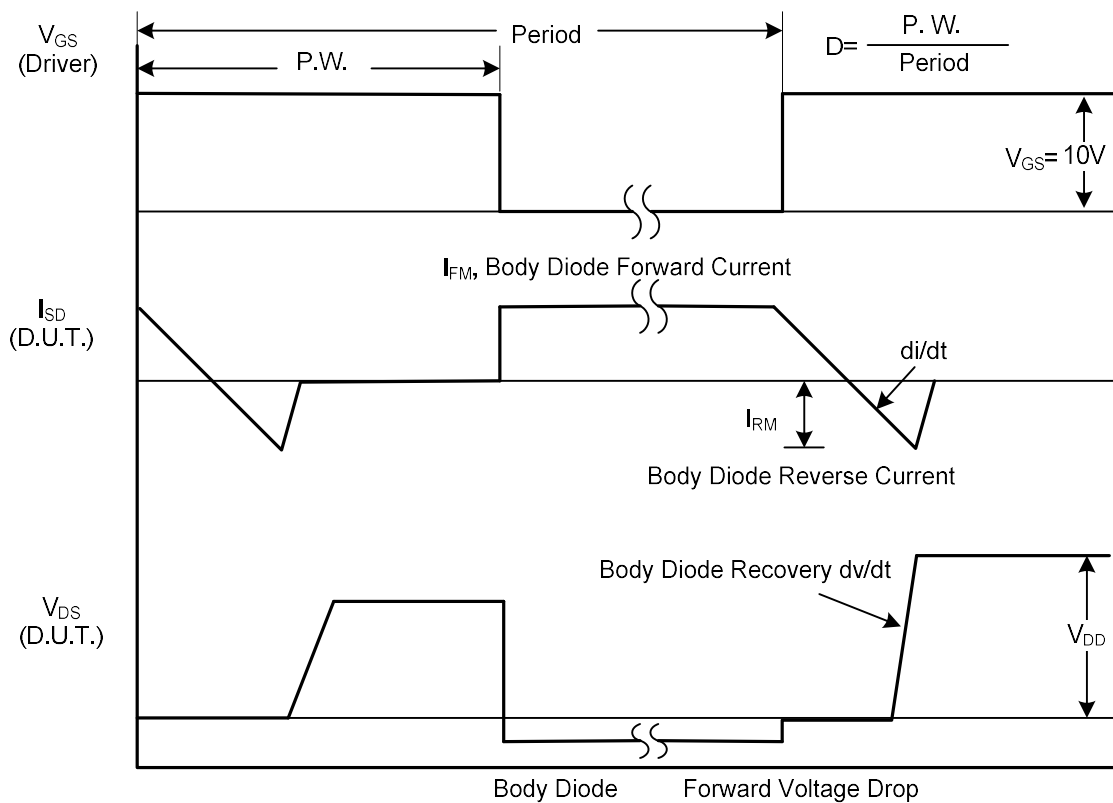
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

TEST CIRCUITS AND WAVEFORMS



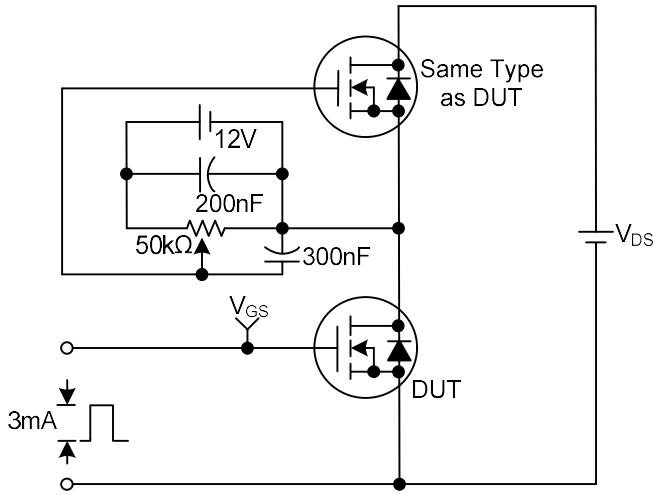
Peak Diode Recovery dv/dt Test Circuit



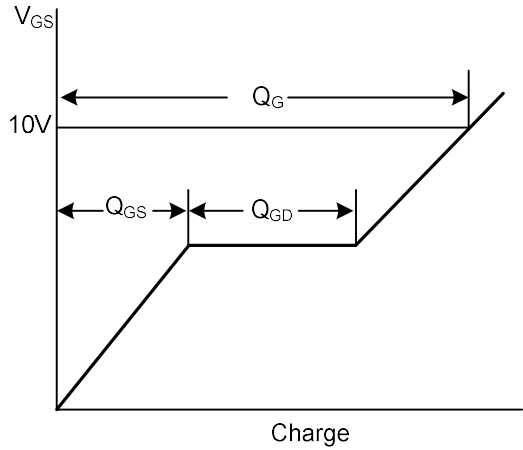
Peak Diode Recovery dv/dt Waveforms

TEST CIRCUITS AND WAVEFORMS

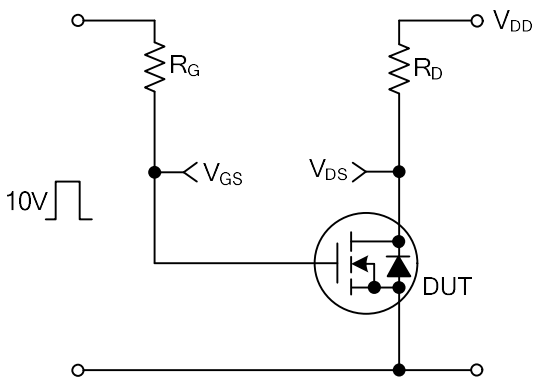
Gate Charge Test Circuit



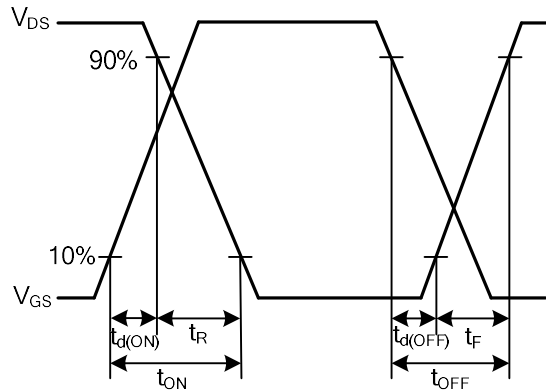
Gate Charge Waveforms



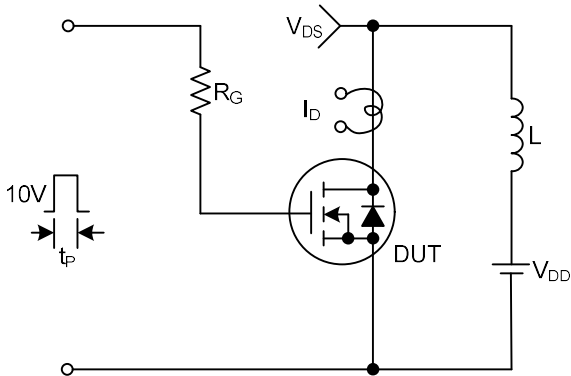
Resistive Switching Test Circuit



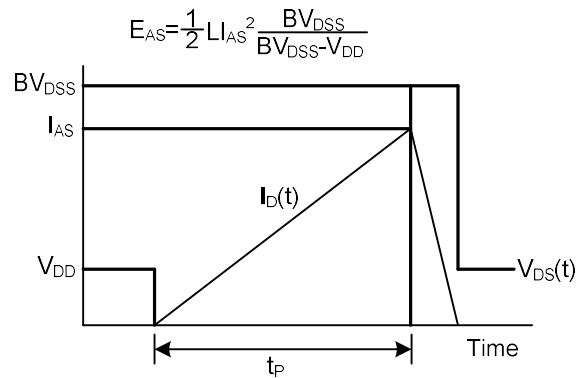
Resistive Switching Waveforms



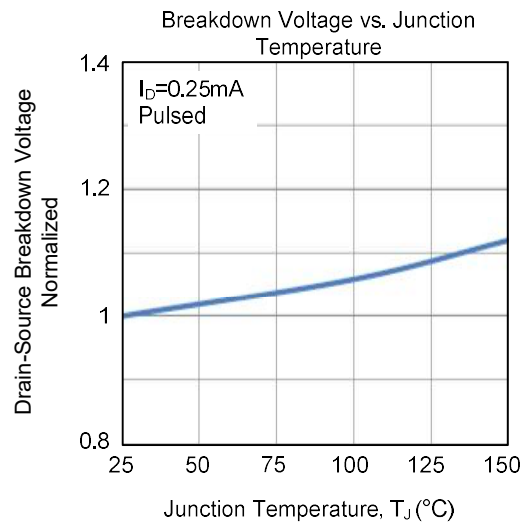
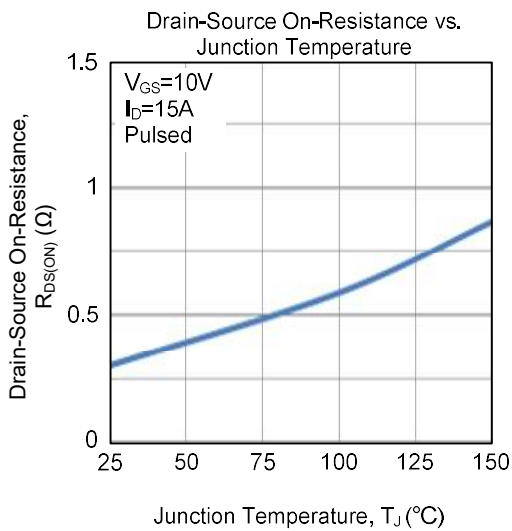
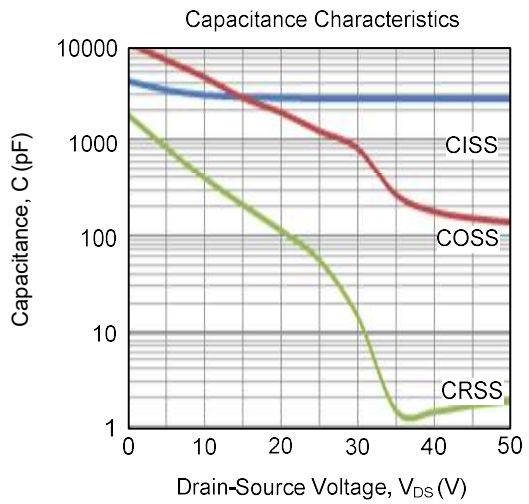
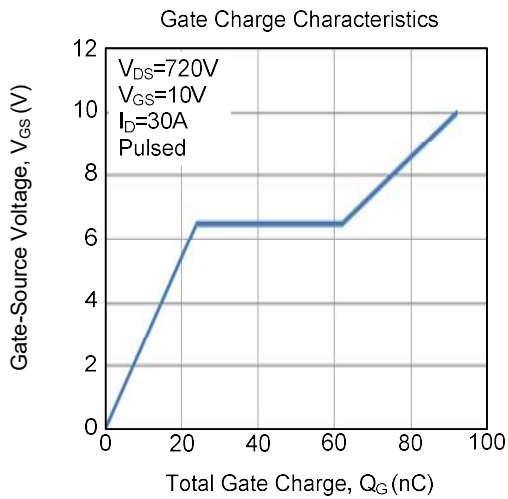
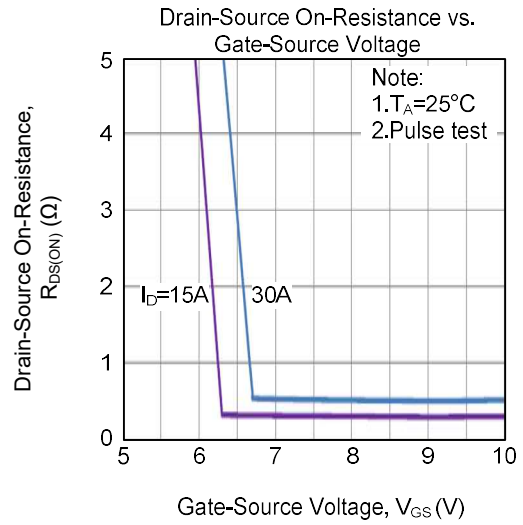
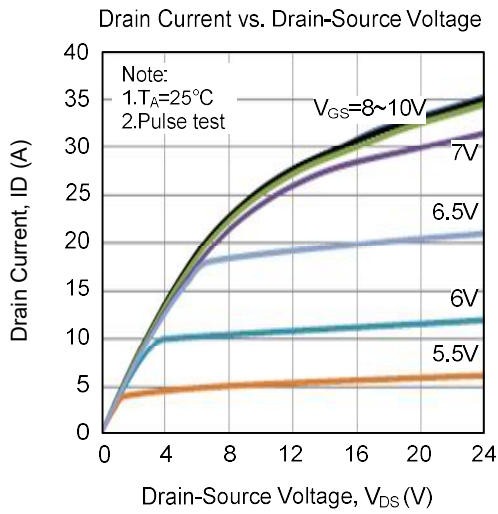
Unclamped Inductive Switching Test Circuit



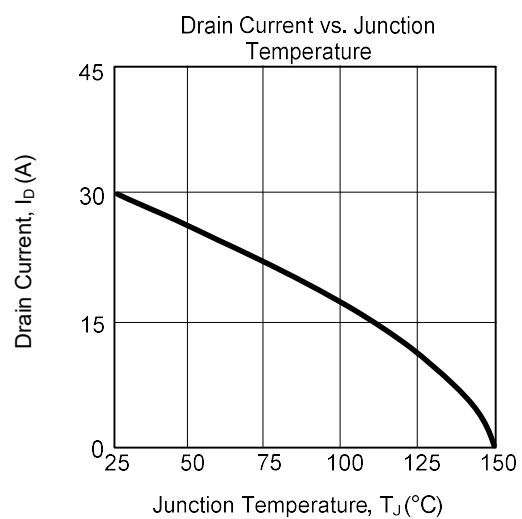
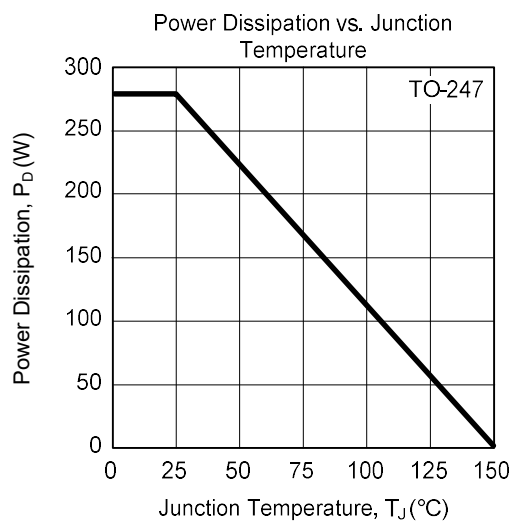
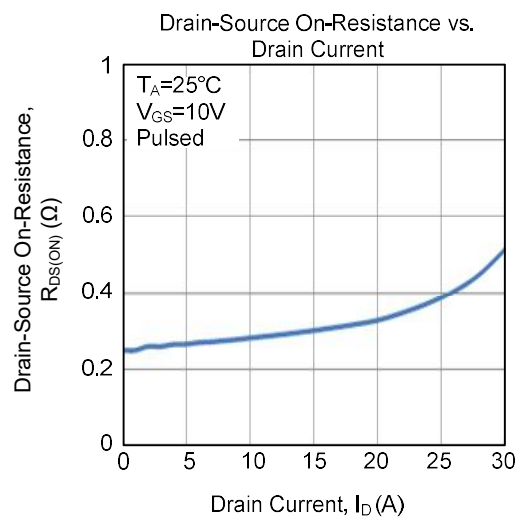
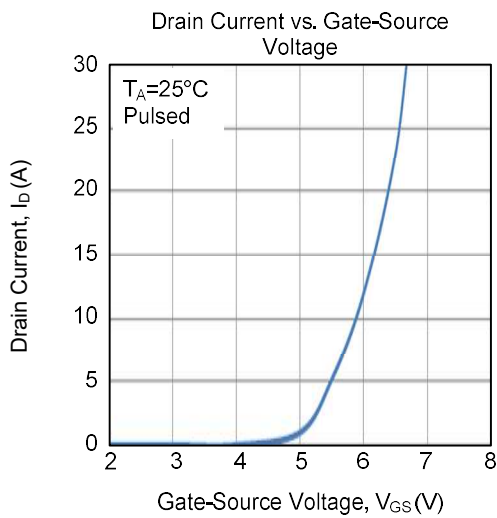
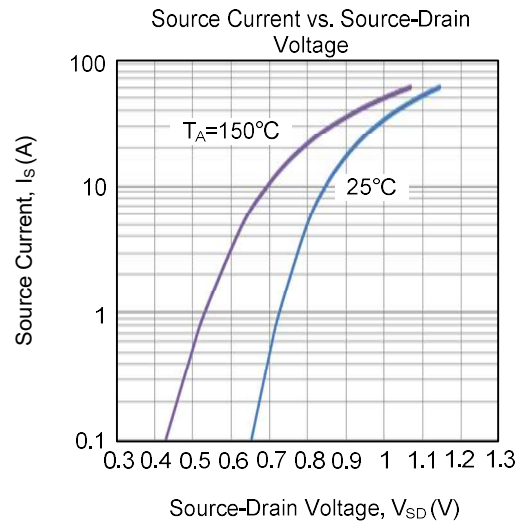
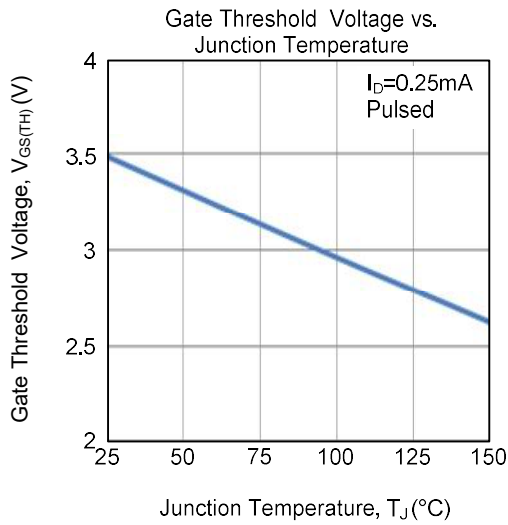
Unclamped Inductive Switching Waveforms



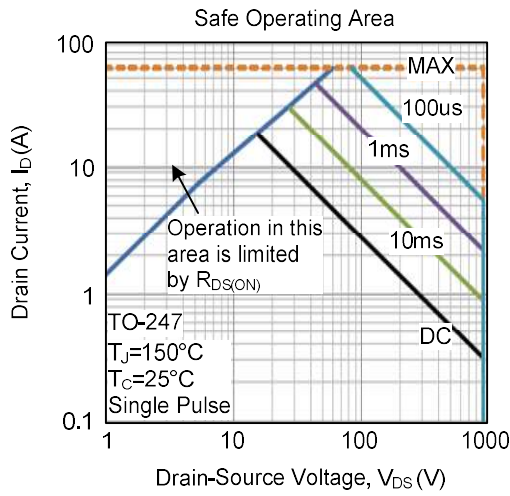
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ **TYPICAL CHARACTERISTICS (Cont.)**



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